IN THE CLAIMS:

Please cancel claims 1-20 and add new claims 21-39 as follows:

1. (Cancelled) A method of growing a thin film onto a substrate located within a reaction chamber comprising feeding a precursor of said film into said reaction chamber, causing said precursor to adsorb onto the surface of the substrate to form a layer thereof, and feeding a catalyst into said reaction chamber in an amount to substantially convert said layer of said precursor to said thin film.

2. (Cancelled) The method of claim 1 wherein any non-adsorbed precursor is removed from the proximity of the substrate before feeding the catalyst into the reaction chamber.

3. (Cancelled) The method of claim 1 wherein subsequent to feeding the catalyst into the reaction chamber the catalyst is removed from the proximity of the substrate.

4. (Cancelled) The method of claim 1 wherein said steps of feeding the precursor, removing excess precursor, feeding a catalyst, and removing catalyst and unwanted reaction products, are repeated to achieve a desired film thickness on said substrate.

5. (Cancelled) The method of claim 3 wherein a purge gas is fed into said reaction space after said precursor but before said catalyst is fed to said reaction space.

6. (Cancelled) The method of claim 5 wherein said purge gas is also introduced into said reaction space after said catalyst but before said precursor of a subsequent deposition cycle is fed to said reaction space.

7. (Cancelled) The method of claim 1 wherein a carrier gas is introduced into said reaction chamber continuously during the practice of said method, whereby the carrier gas functions as a purge gas for said reaction chamber.

8. (Cancelled) The method of claim 1 wherein said precursor comprises hexafluoracetylacetonate - Cu - trimethylvinylsilane.

9. (Cancelled) The method of claim 8 wherein said catalyst comprises water and said film comprises copper.

10. (Cancelled) The method of claim I wherein said substrate is heated.

11. (Cancelled) A method of forming a copper film on a substrate comprising feeding a precursor of hexafluoracetylacetonate - Cu - trimethylvinylsilane into a reaction chamber, causing said precursor to adsorb onto the surface of said substrate to form a layer thereof, and feeding water as a catalyst into said reaction chamber in an amount to substantially form said copper film pursuant to the following reaction:

$$2(hfac) - Cu - (TMVS) \rightarrow Cu^{\circ} + Cu(hfac)_2 \pm 2TMVS.$$

12. (Cancelled) A method of growing a thin film onto a substrate located with a reaction chamber comprising feeding a precursor of said film into said reaction chamber, causing said precursor to adsorb onto the surface of the substrate to form a layer thereof, and feeding a catalyst and said precursor into said reaction chamber in amounts to substantially convert said layer of said precursor to said thin film.

13. (Cancelled) The method of claim 12 wherein any non-adsorbed precursor is removed from the proximity of the substrate before feeding the catalyst and precursor into the reaction chamber.

14. (Cancelled) The method of claim 12 wherein subsequent to the step of feeding precursor and catalyst into the reaction chamber the catalyst, residual precursor, if any, and unwanted reaction products, if any, are removed from the reaction chamber.

15. (Cancelled) The method of claim 14 wherein said steps of feeding the precursor, removing excess precursor, if any, feeding the catalyst and the precursor, and removing the catalyst and excess precursor, if any, and unwanted reaction products, if any, are repeated to achieve a desired film thickness on said substrate.

16. (Cancelled) The method of claim 12 wherein purge gas is fed into said reaction chamber after said precursor but before said catalyst and precursor are fed to said reaction chamber.

17. (Cancelled) The method of claim 16 wherein said purge gas is also introduced into said reaction chamber after said catalyst and precursor are simultaneously introduced, but before said precursor of a subsequent deposition cycle is fed to said reaction chamber.

18. (Cancelled) The method of claim 12 wherein purge gas is introduced into said reaction chamber continuously during the practice of said method, whereby the purge gas functions as a carrier gas.

19. (Cancelled) The method of claim 12 wherein said precursor comprises hexafluoracetylacetonate - Cu - trimethylvinylsilane.

20. (Cancelled) The method of claim 19 wherein said catalyst comprises water and said film comprises copper.

21. (New) A method for depositing a film to a substrate within a process chamber by an atomic layer deposition technique, comprising:

introducing a precursor to the process chamber;

absorbing the precursor to the substrate;

purging the process chamber with a purge gas;

introducing a process gas comprising the precursor and a reactant;

reacting the absorbed precursor with the process gas to deposit the film; and

purging the process chamber with the purge gas.

22. (New) The method of claim 21, wherein the film comprises copper.

23. (New) The method of claim 22, wherein the precursor comprises a copper precursor.

24. (New) The method of claim 23, wherein the copper precursor is copperhexafluoracetylacetonate trimethylvinylsilane.

25. (New) The method of claim 23, wherein the reactant comprises water.

26. (New) The method of claim 25, wherein the purge gas is selected from the group consisting of argon, nitrogen, hydrogen and combinations thereof.

27. (New) A method for depositing a metal-containing film to a substrate within a process chamber by an atomic layer deposition technique, comprising:

introducing a metal-containing precursor to the process chamber;

absorbing the metal-containing precursor to the substrate;

purging the process chamber with a purge gas;

introducing a process gas comprising the metal-containing precursor and a gaseous catalyst;

chemically reducing the absorbed metal-containing precursor with the process gas to deposit the metal-containing film; and

purging the process chamber with the purge gas.

28. (New) The method of claim 27, wherein the metal-containing film comprises copper.

29. (New) The method of claim 28, wherein the metal-containing precursor comprises a copper precursor.

30. (New) The method of claim 29, wherein the copper precursor is copperhexafluoracetylacetonate trimethylvinylsilane.

31. (New) The method of claim 29, wherein the gaseous catalyst comprises water.

32. (New) The method of claim 31, wherein the purge gas is selected from the group consisting of argon, nitrogen, hydrogen and combinations thereof.

33. (New) A method for depositing a copper-containing film to a substrate within a process chamber by an atomic layer deposition technique, comprising:

introducing a copper precursor to the process chamber;

absorbing the copper precursor to the substrate;

purging the process chamber with a purge gas;

introducing a process gas comprising the copper precursor and a reactant;

reacting the absorbed copper precursor with the process gas; and

purging the process chamber with the purge gas.

34. (New) The method of claim 33, wherein the copper precursor is copperhexafluoracetylacetonate trimethylvinylsilane.

35. (New) The method of claim 33, wherein the reactant comprises water.

36. (New) The method of claim 34, wherein the reactant comprises water.

37. (New) The method of claim 35, wherein the purge gas is selected from the group consisting of argon, nitrogen, hydrogen and combinations thereof.

38. (New) A method of growing a thin film onto a substrate located with a reaction chamber comprising feeding a precursor of the film into the reaction chamber, causing the precursor to adsorb onto the surface of the substrate to form a layer thereof, and feeding a catalyst and the precursor into the reaction chamber in amounts to substantially convert the layer of the precursor to the thin film, wherein the precursor comprises copperhexafluoracetylacetonate trimethylvinylsilane.

39. (New) The method of claim 38, wherein the catalyst comprises water and the film comprises copper.